



In re PATENT APPLICATION OF

Tomohisa HOSHINO et al.

Appln. No.: 09/835,820

Filed: April 17, 2001

Confirmation No.: 5539

Group Art Unit: 2825

Examiner: LUU, Chuong A

7/A Amolt
4-19-02
A. Welch

Title: FABRICATION PROCESS OF A SEMICONDUCTOR DEVICE INCLUDING A CVD
PROCESS OF A METAL FILM

April 16, 2002

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AMENDMENT

Hon. Commissioner of Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated January 16, 2002, please amend the above
identified application as follows:

IN THE CLAIMS:

Please enter the following amended claims:

A' 2. (Amended) A method as claimed in claim 1, wherein said first reducing gas
atmosphere is selected from the group consisting of: silane, ammonia and hydrogen.

A 2 sub Bro 4. (Amended) A method as claimed in claim 1, wherein said second reducing
gas atmosphere includes hydrogen.

See the attached Appendix for the changes made to effect the above claim(s).